## REMARKS

Claims 19 and 28 have been amended to place the language "to produce a strain compensated p+ layer" at the place in the claim where the germanium concentration is listed to more clearly set forth that this is the difference over the prior art. Appreciation is expressed to the Examiner who entered amendments to these claims in the Office Action mailed April 6, 2005. Entry of the amendments is earnestly solicited.

The Examiner has also rejected claims 19-21 and 28-30 under 35 U.S.C.§103 as obvious over Wu et al. (hereinafter Wu) in view of Radamson et al. (hereinafter Radamson) Applicants respectfully traverse this rejection for the following reasons.

Wu does not suggest or disclose the formation of a strain compensated p+ layer. Radamson is cited (page 1397, left hand column) to show that Ge concentrations result in a strain compensated layer. However, Radamson in fact teaches that Si-Ge alloys contain strain and Radamson adds Boron as a dopant to compensate for the strain. Claims 19 and 28, by contrast, recite that a p+ layer is placed on the first side of said substrate, said p+ having a boron content of greater than $7x10^{19}$ $cm^{-3}$ to produce a strain compensated p+ layer and a germanium content of no more than about $1x10^{21}$ $cm^{-3}$.

Wu has no strain compensated layer and, as noted in other responses, Wu does not have an etch stop until Wu has a Si-Ge alloy. This has never been controverted. Wu does not have a low Ge etch stop. Applicants do.

Radamson uses boron to strain compensate a Si-Ge alloy. One does not know if this functions as an etch stop, since that is not the purpose of the silicon structures produced in Radamson. One does know that Ge is NOT used to create a strain compensated p+ layer.

Thus a reading of both references, alone or in combination, relates only to Si-Ge alloys and not to lightly doped silicon as claimed herein. One skilled in the art would see both Wu and Radamson as relating only to Si-Ge alloys and not to Si wafers that are only dopedwith a small amount of Ge. The materials are different in kind. To modify either Wu or Radamson to reject the taught Si-Ge alloy and resort to a Si wafer with not enough Ge to form an alloy is improper. Even then, there is absolutely no suggestion in either